

PATENT ABSTRACTS OF JAPAN

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(54) METHOD FOR REMOVING PHOTORESIST FILM

(57)Abstract:

PURPOSE: To allow quick removal of photoresist film through simple wet method without relying on the plasma ashing by subjecting the photoresist formed on the surface of a substrate to freezing prior to removal thereof.

CONSTITUTION: Liquid nitrogen is dripped, by a small quantity at a time, onto a photoresist film formed on the surface of a silicon wafer thus freezing and cracking the photoresist film. The silicon wafer is then immersed into methanol filling a cleaning tank and subjected to ultrasonic cleaning thus dissolving the photoresist film immediately into methanol. It is then washed with water thus obtaining a silicon wafer from which the photoresist film is removed. Alternatively, the photoresist film may be frozen by immersing the substrate into a refrigerant or bringing the photoresist film on the surface of substrate into contact with vapor of refrigerant, and the freezing time of 10sec-3min is normally sufficient.

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